

Product Summary

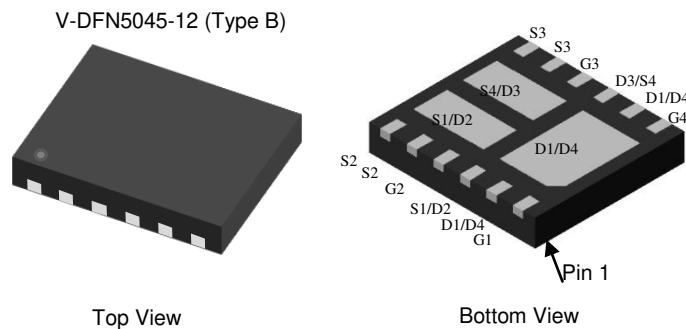
BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
60V	22mΩ @ V _{GS} = 10V	10.6A
	30mΩ @ V _{GS} = 4.5V	8.7A

Description

This new generation complementary MOSFET H-Bridge features low on-resistance achievable with low gate drive.

Applications

- Motor Control
- DC-DC Converters
- Power Management

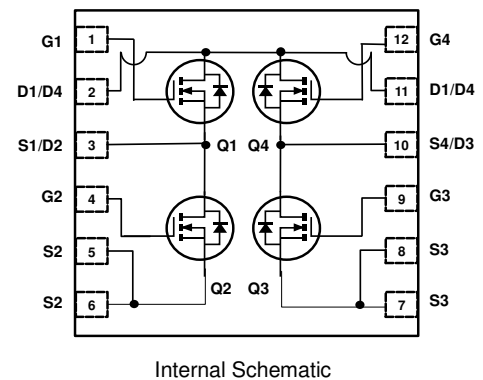


Features

- Thermally Efficient Package – Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**

Mechanical Data

- Case: V-DFN5045-12 (Type B)
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.097 grams (Approximate)

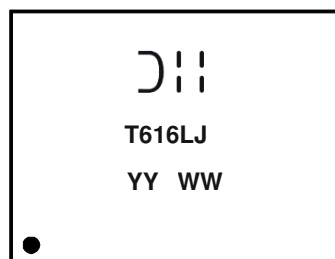


Ordering Information (Note 4)

Part Number	Case	Packaging
DMHT6016LFJ-13	V-DFN5045-12 (Type B)	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



= Manufacturer's Marking
 T616LJ = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 16 = 2016)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State I _D	T _A = +25°C	10.6
		T _A = +70°C	8.5
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	t < 10s I _D	T _A = +25°C	14.8
		T _A = +70°C	11.9
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	60	A
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	2	A
Avalanche Current (Note 7) L=0.1mH	I _{AS}	15.3	A
Avalanche Energy (Note 7) L=0.1mH	E _{AS}	11.7	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	1.16	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State R _{θJA}	t < 10s	108
			56
Total Power Dissipation (Note 6)	P _D	2.7	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State R _{θJA}	t < 10s	46
			24
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	4.4	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 48V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	17	22	mΩ	V _{GS} = 10V, I _D = 10A
		—	22.2	30		V _{GS} = 4.5V, I _D = 6A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	864	—	pF	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{OSS}	—	282	—		
Reverse Transfer Capacitance	C _{RSS}	—	27	—		
Gate Resistance	R _G	—	1.3	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _G	—	8.4	—	nC	V _{DS} = 30V, I _D = 10A
Total Gate Charge (V _{GS} = 10V)	Q _G	—	17	—		
Gate-Source Charge	Q _{GS}	—	3.1	—		
Gate-Drain Charge	Q _{GD}	—	4.3	—		
Turn-On Delay Time	t _{D(ON)}	—	3.4	—	ns	V _{GS} = 10V, V _{DS} = 30V, R _G = 6Ω, I _D = 10A
Turn-On Rise Time	t _R	—	5.2	—		
Turn-Off Delay Time	t _{D(OFF)}	—	13	—		
Turn-Off Fall Time	t _F	—	7	—		
Reverse Recovery Time	t _{RR}	—	22	—	ns	I _F = 10A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	—	11	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

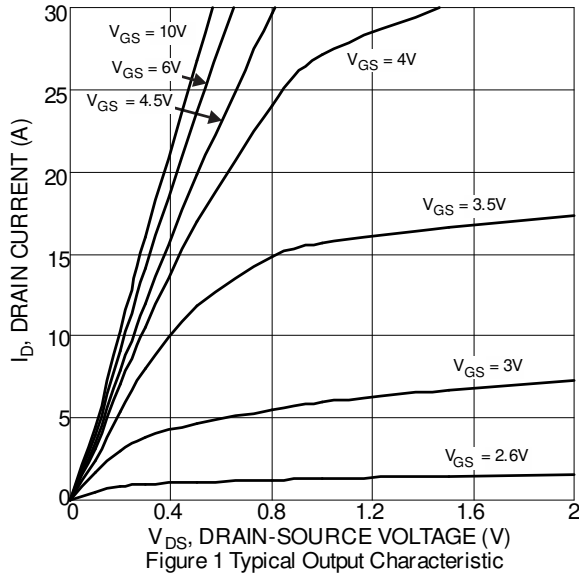


Figure 1 Typical Output Characteristic

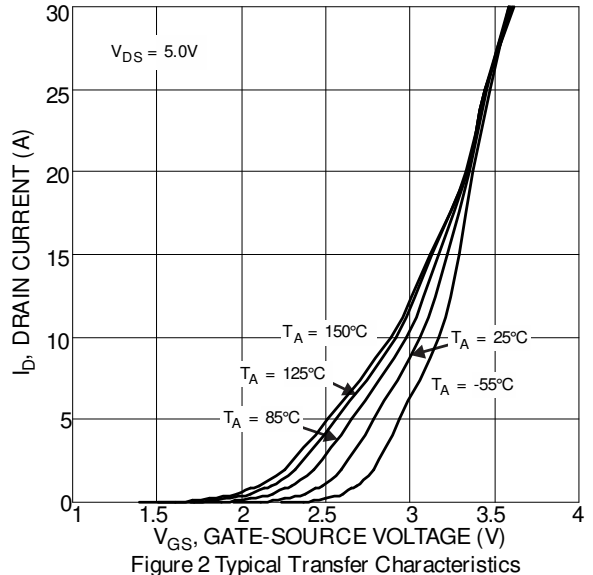


Figure 2 Typical Transfer Characteristics

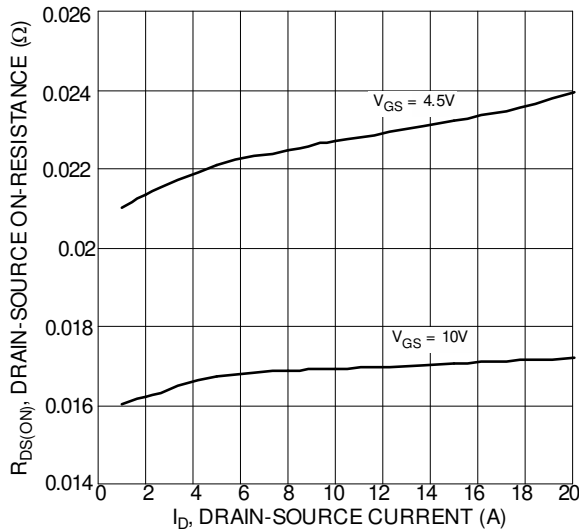


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

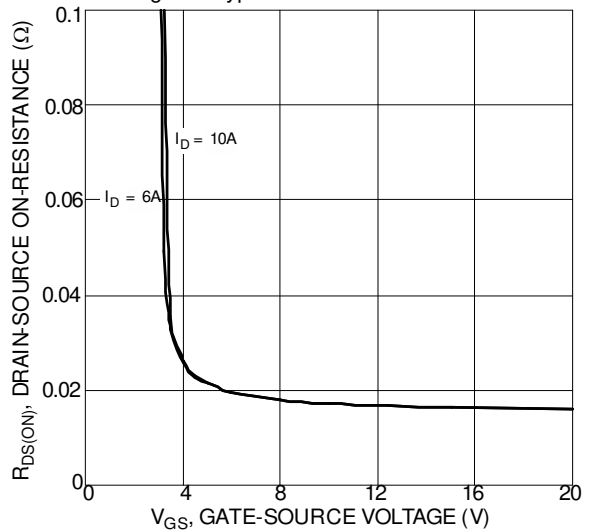


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

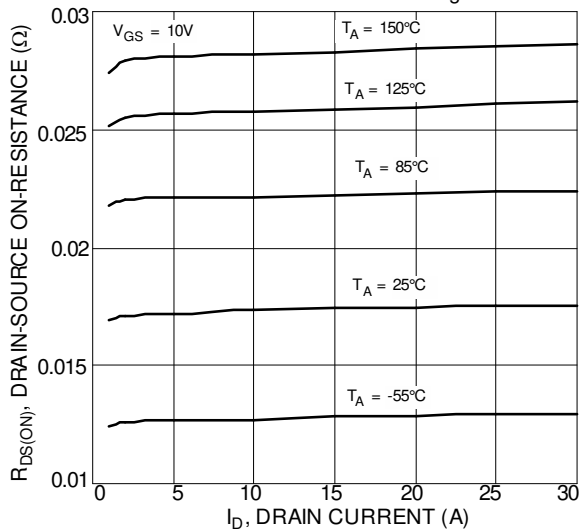


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

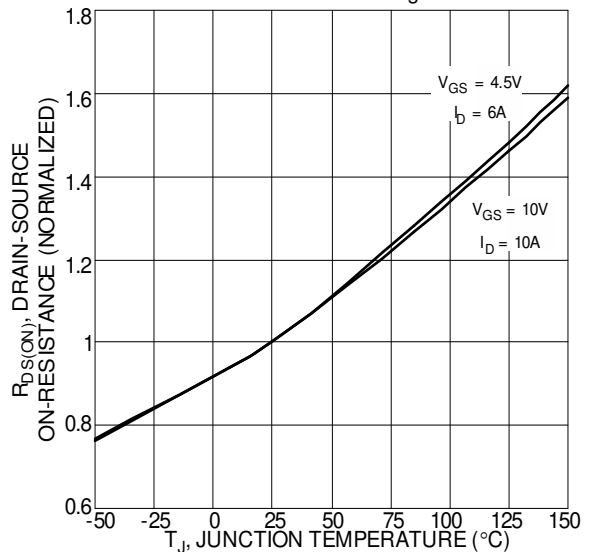


Figure 6 On-Resistance Variation with Temperature

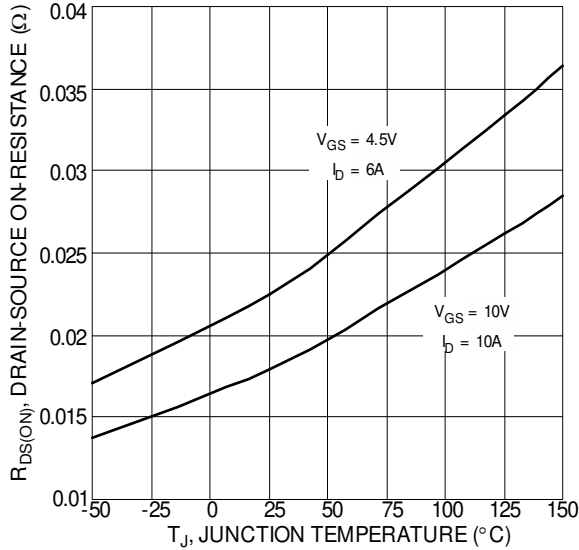


Figure 7 On-Resistance Variation with Temperature

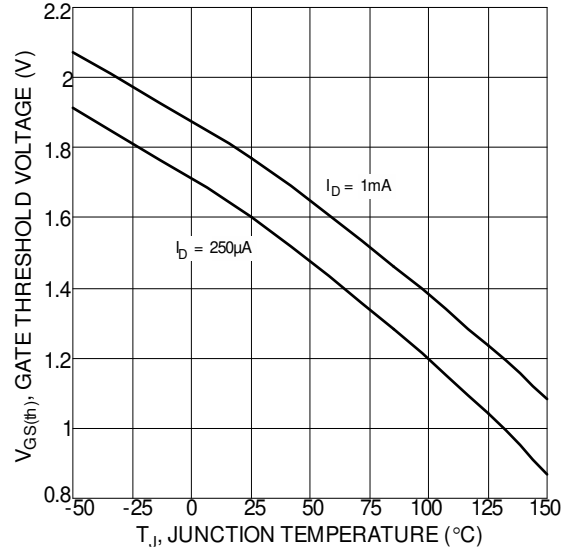


Figure 8 Gate Threshold Variation vs. Temperature

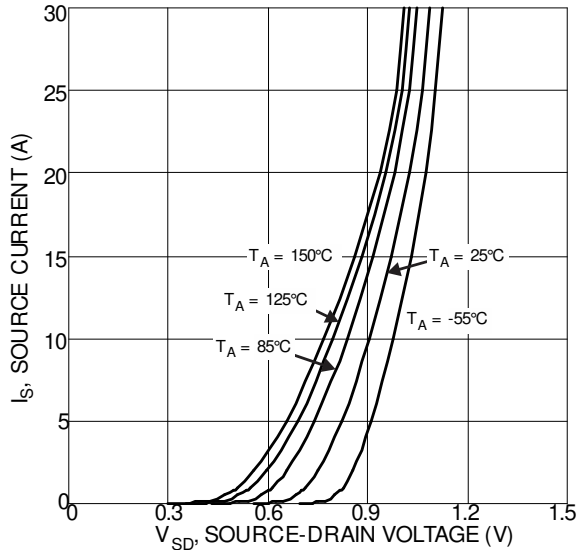


Figure 9 Diode Forward Voltage vs. Current

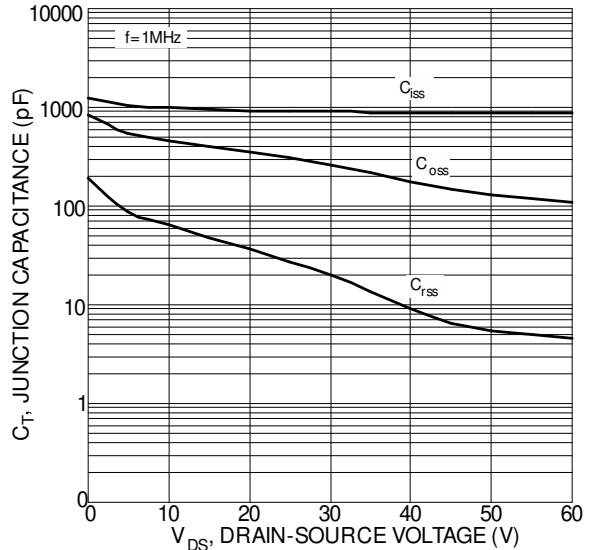


Figure 10 Typical Junction Capacitance

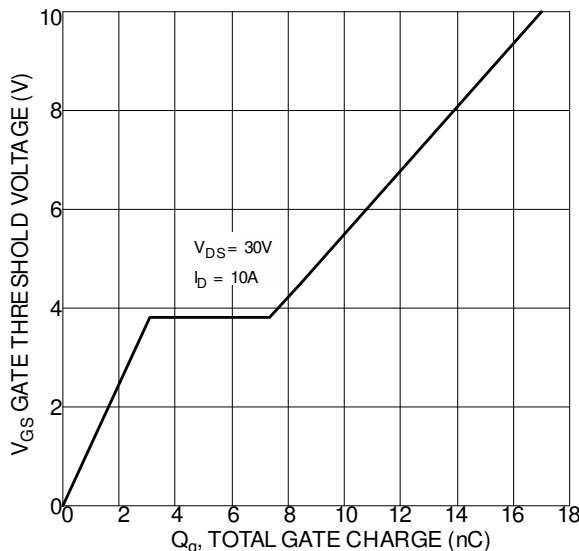


Figure 11 Gate Charge

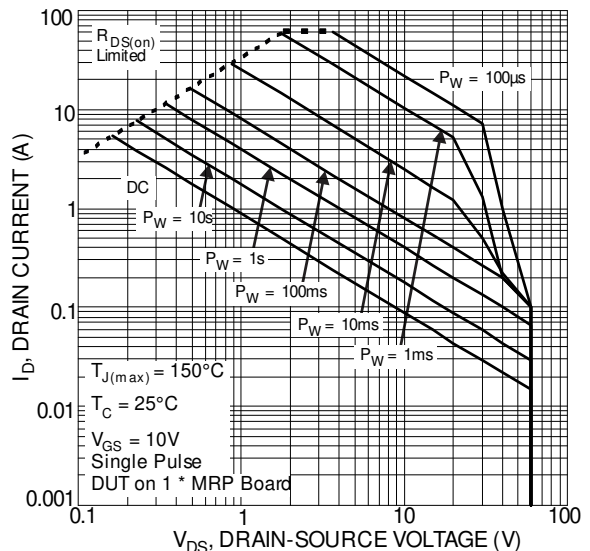
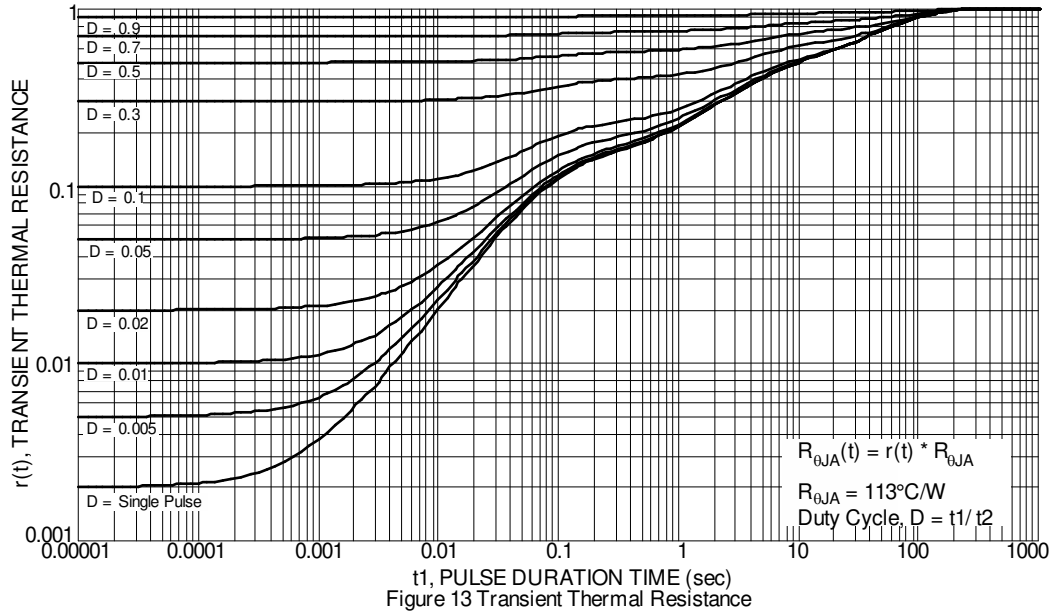


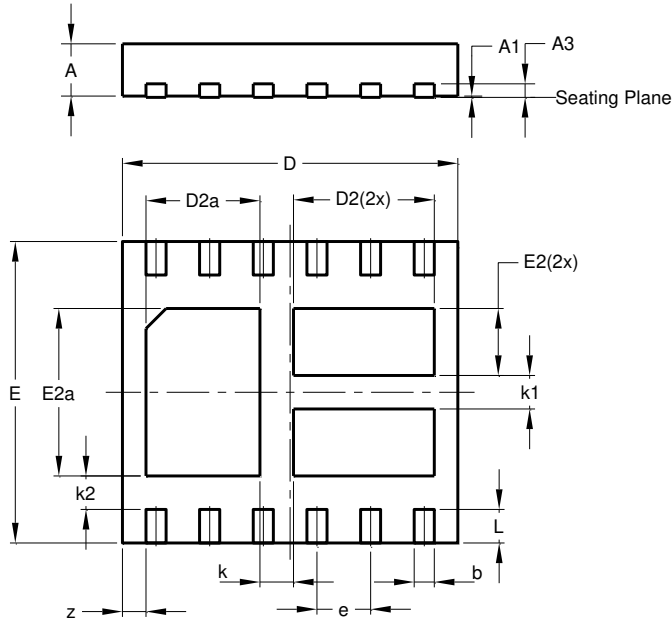
Figure 12 SOA, Safe Operation Area



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

V-DFN5045-12 (Type B)



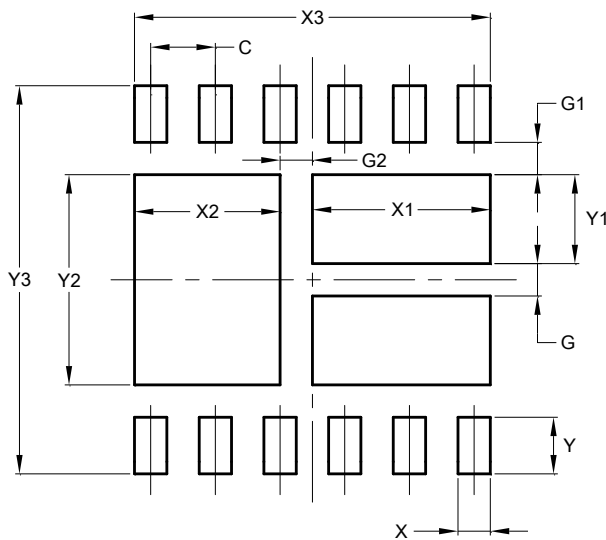
V-DFN5045-12 (Type B)			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.25	0.35	0.30
D	4.95	5.05	5.00
D2	2.00	2.20	2.10
D2a	1.60	1.80	1.70
E	4.45	4.55	4.50
E2	0.90	1.10	1.00
E2a	2.40	2.60	2.50
e	-	-	0.80
k	-	-	0.50
k1	-	-	0.50
k2	-	-	0.50
L	0.45	0.55	0.50
z	-	-	0.35

All Dimensions in mm

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

V-DFN5045-12 (Type B)



Dimensions	Value (in mm)
C	0.800
G	0.40
G1	0.40
G2	0.40
X	0.40
X1	2.20
X2	1.80
X3	4.40
Y	0.700
Y1	1.100
Y2	2.600
Y3	4.800

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